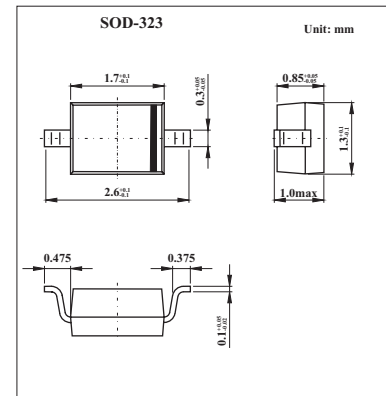


## Silicon Epitaxial Planar Diode

## 1SV216

## ■ Features

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Peak Reverse Voltage	$V_{RM}$	35 ( $R_L = 10\text{K } \Omega$ )	V
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	$V_R$	$I_R = 1 \mu\text{A}$	30			V
Reverse Current	$I_R$	$V_R = 28\text{V}$			10	nA
Capacitance	$C_{2V}$	$f = 1\text{MHz}; V_R = 2\text{V}$	10.5		16	pF
	$C_{10V}$	$f = 1\text{MHz}; V_R = 10\text{V}$	3.3		5.7	
Capacitance Ratio	$C_{2V}/C_{10V}$		2.5		3.4	
Series Resistance	$r_s$	$V_R = 5\text{V}, f = 470\text{MHz}$		0.55	1.2	$\Omega$

## ■ Marking

Marking	T4